



60V 175°C PNP LOW SAT MEDIUM POWER TRANSISTOR IN POWERDI5060-8

Features

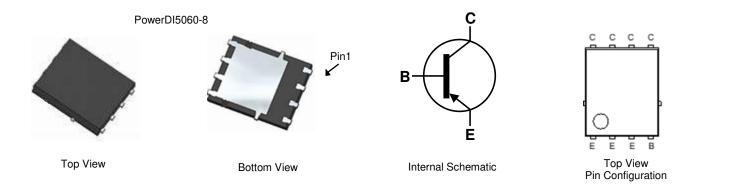
- BV_{CEO} > -60V
- I_C = -3A Continuous Collector Current
- I_{CM} = -8A Peak Pulse Current
- R_{CE(SAT)} < 120 mΩ
- Rated to +175°C—Ideal for High Ambient Temperature Environments
- Complementary Part DXTN3C60PS
- Meets Stringent Requirements of Automotive Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: PowerDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Finish—Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

Applications

- Power Management
- Load Switch
- Linear Mode Voltage Regulator
- Backlighting Applications



Ordering Information

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DXTP3C60PSQ-13	Automotive	DXTP3C60PS	13	12	2500

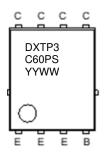
Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

Marking Information



DXTP3 = Product Type Marking Code C60PS = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 18 = 2018) WW = Week Code (01 to 53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-7	V
Base Current	IB	-1	A
Continuous Collector Current	Ic	-3	A
Peak Pulse Collector Current	I _{CM}	-8	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	PD	5	W	
Thermal Desistance, lunction to Ambient	(Note 5)		40	<u>^0</u> /11/	
Thermal Resistance, Junction to Ambient	(Note 6)	– R _{ÐJA}	120	°C/W	
Thermal Desistance, lunction to Coop	(Note 5, 7)		2	0000	
Thermal Resistance, Junction to Case	(Note 6, 7)	- R _{ejc}	12	°C/W	
Operating and Storage Temperature Range		TJ, T _{STG}	-55 to +175	°C	

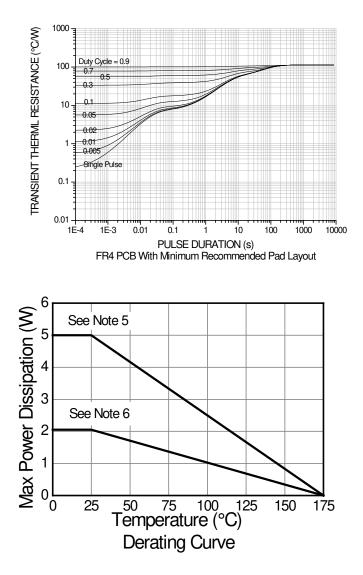
ESD Ratings (Note 8)

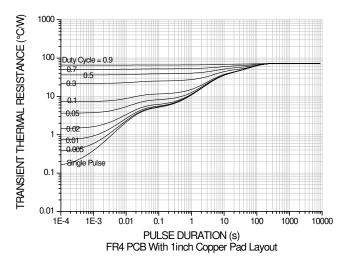
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	8000V	V	ЗA
Electrostatic Discharge—Machine Model	ESD MM	400V	V	С

Notes: 5. For a device mounted with the collector lead on 25mm × 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; the device is measured under still For a device mounted with the collector lead on 25mm × 25mm 202 copp air conditions whilst operating in a steady-state.
Same as Note 6 except mounted on minimum recommended pad layout.
Thermal resistance from junction to the top of the case.
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Typical Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)







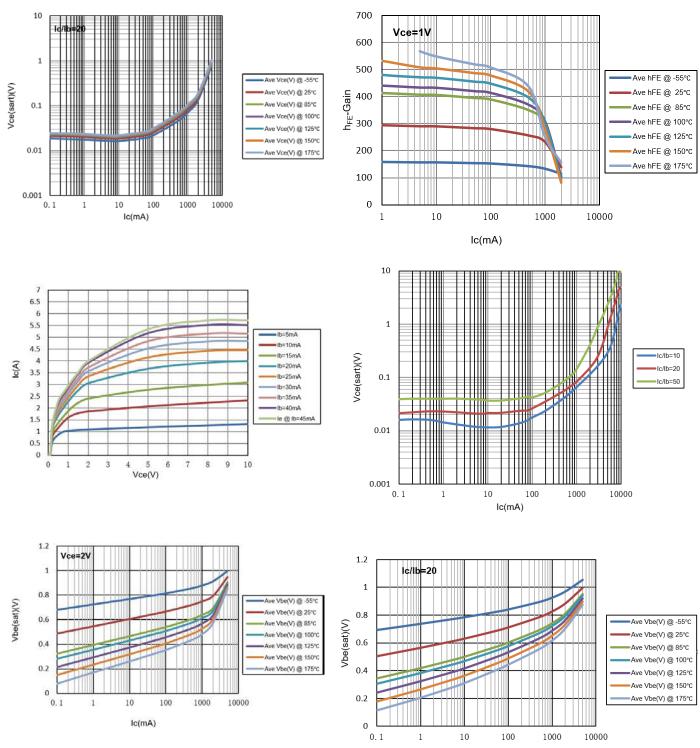
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Мах	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-60	_	—	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-60	_	—	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	—	—	V	I _E = -100μA
Collector-Base Cutoff Current		_	_	-100	nA	V _{CB} = -48V
Collector-Base Cuton Current	ICBO	—	—	-50	μA	V _{CB} = -48V @ Tj = 150°C
Emitter Cutoff Current	I _{EBO}	—	—	100	nA	V _{EB} = -7V
		_	-2.5	100		$V_{CES} = -48V, T_A = +25^{\circ}C$
Collector-Emitter Cutoff Current	ICES	—	-2.4	-	nA	$V_{CES} = -14V, T_A = +40^{\circ}C$
		—	-50	—		$V_{CES} = -14V, T_A = +105^{\circ}C$
ON CHARACTERISTICS (Note 9)	1		r	1	r	
		150	250			$I_{C} = -500 \text{mA}, V_{CE} = -2 \text{V}$
DC Current Gain	h _{FE}	150	225		—	$I_{C} = -1A, V_{CE} = -2V$
	UFE	80	130	—		$I_{C} = -2A, V_{CE} = -2V$
		35	75	—		$I_{C} = -3A, V_{CE} = -2V$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	-100	-225	mV	$I_{\rm C} = -1A, I_{\rm B} = -50 {\rm mA}$
Conector-Enniter Saturation Voltage		_	-240	-360		$I_{C} = -3A, I_{B} = -300mA$
Collector-Emitter Saturation Resistance	Barren	_	100	225	mΩ	$I_{\rm C} = -1A, I_{\rm B} = -50 {\rm mA}$
	R _{CE(sat)}	_	80	120		$I_{C} = -3A, I_{B} = -300mA$
Base-Emitter Saturation Voltage	Varia	_	-0.8	-0.95	V	$I_{C} = -1A, I_{B} = -50mA$
	V _{BE(sat)}	_	-1.02	-1.2		$I_{C} = -2A, I_{B} = -200mA$
Base-Emitter Turn-On Voltage	V _{BE(on)}	_	-0.7	-0.8	V	$I_{C} = -0.5A, V_{CE} = -2V$
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f _T	—	135	—	MHz	$V_{CE} = -10V, I_{C} = -100mA, f = 100MHz$
Output Capacitance	Cobo	_	42	—	pF	V _{CB} = -10V, f = 1МНz
Delay Time	t _d	_	15	—	ns	
Rise Time	tr	_	220	_	ns	
Turn-On Time	t _(on)	_	235	_	ns	V _{CC} = -12.5V, I _C = 3A
Storage Time	ts	—	160	—	ns	I _{B1} = -I _{B2} = -0.150A
Fall Time	t _f	—	185	—	ns	
Turn-Off Time	t _(off)	—	345	—	ns	

Note: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

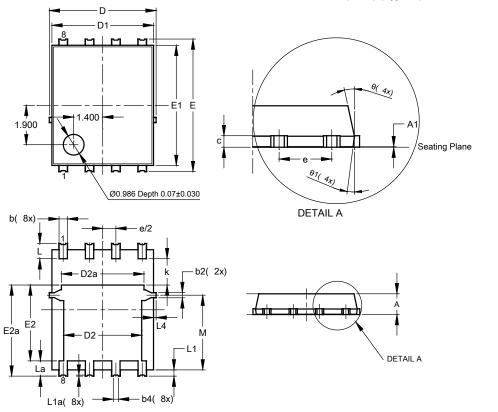


lc(mA)



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

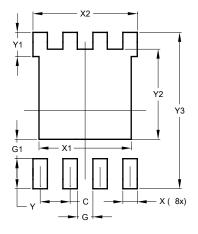


PowerDI5060-8 (SWP) (Type Q) Dim Min Max Тур 1.10 0.90 1.00 Α 0.05 **A1** 0 ---0.30 0.50 0.41 b b2 0.20 0.35 0.25 b4 0.25REF 0.230 0.330 0.277 С D 5.15 BSC D1 4.70 5.10 4.90 D2 3.56 3.96 3.76 D2a 3.78 4.18 3.98 Ε 6.40 BSC 5.60 6.00 5.80 E1 E2 3.46 3.86 3.66 E2a 4.195 4.595 4.395 1.27BSC е 1.05 k ---L 0.635 0.835 0.735 0.635 0.835 0.735 La L1 0.200 0.400 0.300 L1a 0.050REF 0.025 0.225 0.125 L4 3.205 Μ 4.005 3.605 θ 10° 12° 11° θ1 8° 7° 6° All Dimensions in mm

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type Q)



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	4.100			
X2	4.420			
Y	1.270			
Y1	1.020			
Y2	3.810			
Y3	6.610			



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